## 2SC2377

### Silicon NPN epitaxial planar type

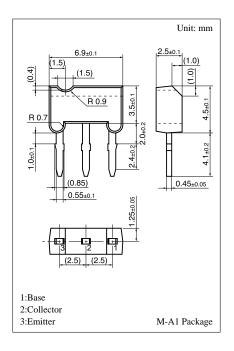
#### For high-frequency amplification

#### Features

- Optimum for RF amplification of FM/AM radios.
- High transition frequency f<sub>T</sub>.
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

#### Absolute Maximum Ratings (Ta=25°C)

| Parameter                    | Symbol    | Ratings           | Unit |
|------------------------------|-----------|-------------------|------|
| Collector to base voltage    | $V_{CBO}$ | 30                | V    |
| Collector to emitter voltage | $V_{CEO}$ | 20                | V    |
| Emitter to base voltage      | $V_{EBO}$ | 3                 | V    |
| Collector current            | $I_{C}$   | 15                | mA   |
| Collector power dissipation  | $P_{C}$   | 400               | mW   |
| Junction temperature         | $T_{j}$   | 150               | °C   |
| Storage temperature          | $T_{stg}$ | <b>−55 ~ +150</b> | °C   |

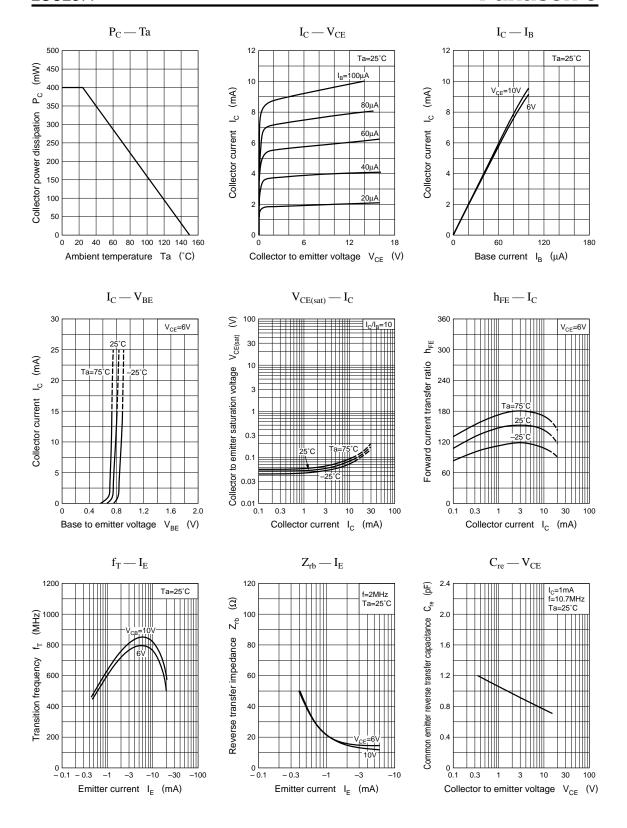


#### Electrical Characteristics (Ta=25°C)

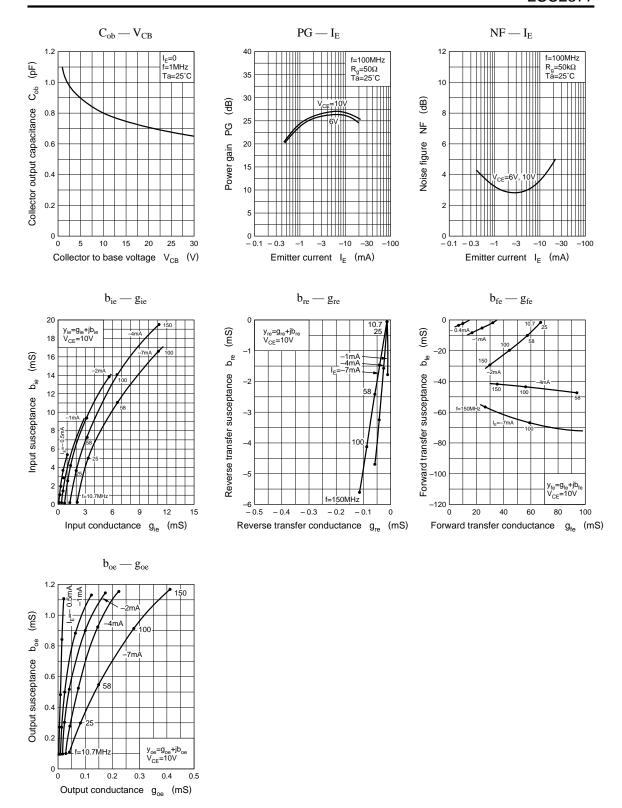
| Parameter                                   | Symbol            | Conditions                              | min | typ | max | Unit |
|---|-------------------|---|-----|-----|-----|------|
| Collector cutoff current                    | $I_{CBO}$         | $V_{CB} = 10V, I_{E} = 0$               |     |     | 100 | nA   |
|   | $I_{CEO}$         | $V_{CE} = 20V, I_B = 0$                 |     |     | 10  | μΑ   |
| Emitter cutoff current                      | $I_{EBO}$         | $V_{EB} = 3V, I_C = 0$                  |     |     | 1   | μΑ   |
| Forward current transfer ratio              | h <sub>FE</sub> * | $V_{CB} = 6V, I_{E} = -1mA$             | 65  |     | 260 |      |
| Base to emitter voltage                     | V <sub>BE</sub>   | $V_{CB} = 6V, I_{E} = -1mA$             |     | 720 |     | mV   |
| Transition frequency                        | $f_{T}$           | $V_{CB} = 6V, I_{E} = -1mA, f = 100MHz$ | 450 | 650 |     | MHz  |
| Noise figure                                | NF                | $V_{CB} = 6V, I_{E} = -1mA$             |     | 3.3 | 5   | dB   |
| Power gain                                  | PG                | $V_{CB} = 6V, I_E = -1mA$               | 20  | 24  |     | dB   |
| Common emitter reverse transfer capacitance | C <sub>re</sub>   | $V_{CE} = 6V, I_C = 1mA$                |     | 0.8 | 1   | pF   |

#### \*hFE Rank classification

| Rank     | С        | D         |
|----------|----------|-----------|
| $h_{FE}$ | 65 ~ 160 | 100 ~ 260 |



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